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BGS8M2

SiGe:C low-noise amplifier MMIC with bypass switch for LTE

Rev. 4 — 13 June 2018
Product data sheet
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1 General description

The BGS8M2 is, also known as the LTE3001M, a Low-Noise Amplifier (LNA) with bypass switch for LTE receiver applications, available in a small plastic 6-pin extremely thin leadless package. The BGS8M2 requires one external matching inductor.

The BGS8M2 delivers system-optimized gain for both primary and diversity applications where sensitivity improvement is required. The high linearity of these low noise devices ensures the required receive sensitivity independent of cellular transmit power level in FDD (Frequency Division Duplex) systems. When receive signal strength is sufficient, the BGS8M2 can be switched off to operate in bypass mode at a 1 µA current, to lower power consumption.

The BGS8M2 is optimized for 1805 MHz to 2200 MHz.

2 Features and benefits

- Operating frequency from 1805 MHz to 2200 MHz
- Noise figure = 0.85 dB
- Gain 14.4 dB
- High input 1 dB compression point of -3.5 dBm
- Bypass switch insertion loss of 2.2 dB
- High in band $IP3_i$ of 3.5 dBm
- Supply voltage 1.5 V to 3.1 V
- Self-shielding package concept
- Integrated supply decoupling capacitor
- Optimized performance at a supply current of 5.8 mA
- Power-down mode current consumption < 1 µA
- Integrated temperature stabilized bias for easy design
- Require only one input matching inductor
- Input and output DC decoupled
- ESD protection on all pins (HBM > 2 kV)
- Integrated matching for the output
- Available in 6-pins leadless package 1.1 mm x 0.7 mm x 0.37 mm; 0.4 mm pitch: SOT1232
- 180 GHz transit frequency - SiGe:C technology
- Moisture sensitivity level 1

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3 Applications

- LNA for LTE reception in smart phones
- Feature phones
- Tablet PCs
- RF front-end modules

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4 Quick reference data

Table 1. Quick reference data

1805 MHz ≤ f ≤ 2200 MHz, V_{CC} = 2.8 V, $V_{I(CTRL)}$ ≥ 0.8 V and T_{amb} = 25 °C. Input matched to 50 Ω using a 3.9 nH inductor in series. Unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CC}	supply voltage			1.5	-	3.1	V
I_{CC}	supply current	in gain mode		3.8	5.8	7.8	mA
		in bypass mode; $V_{I(CTRL)}$ < 0.3 V		-	-	1	µA
G_p	power gain	in gain mode; f = 1960 MHz	[1] [2]	12.4	14.4	16.4	dB
		in bypass mode; f = 1960 MHz	[1] [2]	-4.0	-2.2	-0.7	dB
NF	noise figure	in gain mode; f = 1960 MHz	[1] [3] [2]	-	0.85	1.4	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	in gain mode; f = 1960 MHz	[1] [2]	-7.5	-3.5	-	dBm
$IP3_i$	input third-order intercept point	in gain mode; f = 1960 MHz	[1] [2]	-1.5	3.5	-	dBm

[1] E-UTRA operating band 2 (1930 MHz to 1990 MHz).
[2] Guaranteed by device design; not tested in production.
[3] PCB losses are subtracted.

5 Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGS8M2	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1.1 x 0.7 x 0.37 mm	SOT1232
OM17006	EVB	BGS8M2 evaluation board	-

6 Marking

Table 3. Marking codes

Type number	Marking code
BGS8M2	N

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7 Block diagram

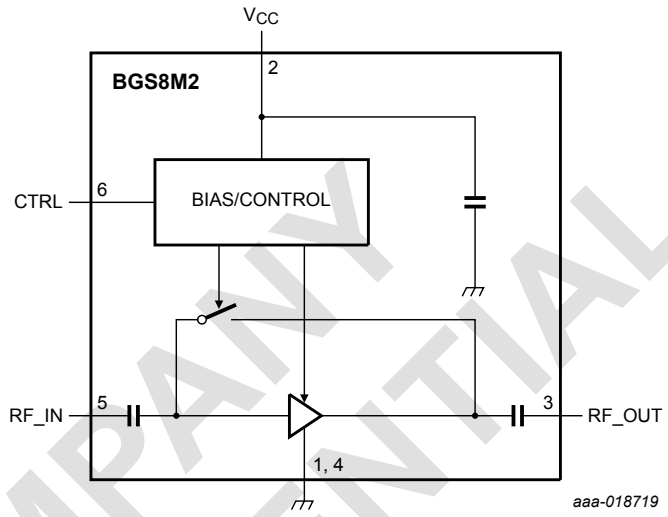


Figure 1. Block diagram

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8 Pinning information

8.1 Pinning

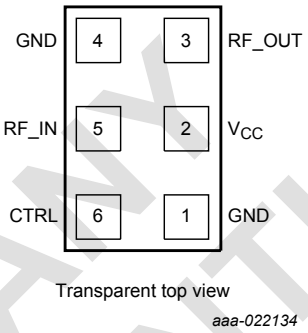


Figure 2. Pin configuration

8.2 Pin description

Table 4. Pinning

Symbol	Pin	Description
GND	1	ground
V_{CC}	2	supply voltage
RF_OUT	3	RF out
GND_RF	4	ground RF
RF_IN	5	RF in
CTRL	6	gain control, switch between gain and bypass mode

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9 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).
See legal section: "disclaimers" paragraph "Limiting values".

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage	RF input AC coupled	[1]	-0.5	+5.0	V
$V_{I(CTRL)}$	input voltage on pin CTRL	$V_{I(CTRL)} < V_{CC} + 0.6$ V	[1][2]	-0.5	+5.0	V
$V_{I(RF_IN)}$	input voltage on pin RF_IN	DC, $V_{I(RF_IN)} < V_{CC} + 0.6$ V	[1][2]	-0.5	+5.0	V
$V_{I(RF_OUT)}$	input voltage on pin RF_OUT	DC, $V_{I(RF_OUT)} < V_{CC} + 0.6$ V	[1][2][3]	-0.5	+5.0	V
P_i	input power		[1]	-	26	dBm
P_{tot}	total power dissipation	$T_{sp} \leq 130$ °C		-	55	mW
T_{stg}	storage temperature			-65	+150	°C
T_j	junction temperature			-	150	°C
V_{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to ANSI/ESDA/JEDEC standard JS-001		-	±2	kV
		Charged Device Model (CDM) according to JEDEC standard JESD22-C101C		-	±1	kV

[1] Stresses with pulses of 1 s in duration. V_{CC} connected to a power supply of 2.8 V with 500 mA current limit.
[2] Warning: Due to internal ESD diode protection, to avoid excess current, the applied DC voltage must not exceed V_{CC} + 0.6 V or 5.0 V.
[3] The RF input and RF output are AC coupled through internal DC blocking capacitors.

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10 Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.5	-	3.1	V
T_{amb}	ambient temperature		-40	+25	+85	°C
$V_{I(CTRL)}$	input voltage on pin CTRL	bypass mode	-	-	0.3	V
		ON state	0.8	-	V_{CC}	V

11 Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			225	K/W

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12 Characteristics

Table 8. Characteristics at V_{CC} = 1.8 V

1805 MHz ≤ f ≤ 2200 MHz, V_{CC} = 1.8 V, $V_{I(CTRL)}$ ≥ 0.8 V and T_{amb} = 25 °C. Input matched to 50 Ω using a 3.9 nH inductor in series. Unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Δφ	phase variation	between gain mode and bypass mode					
		f = 1843 MHz		-	-	-	deg
		f = 1960 MHz	[1]	-5.0	-	+5.0	deg
		f = 2140 MHz		-	-	-	deg
Gain mode							
I_{CC}	supply current			3.6	5.6	7.6	mA
G_p	power gain	f = 1843 MHz	[1][2]	12.3	14.3	16.3	dB
		f = 1960 MHz	[3]	12.0	14.0	16.0	dB
		f = 2140 MHz	[1][3]	11.2	13.2	15.2	dB
RL_{in}	input return loss	f = 1843 MHz	[2]	-	5.5	-	dB
		f = 1960 MHz	[4]	-	6.0	-	dB
		f = 2140 MHz	[3]	-	7.0	-	dB
RL_{out}	output return loss	f = 1843 MHz	[2]	-	11.0	-	dB
		f = 1960 MHz	[4]	-	11.0	-	dB
		f = 2140 MHz	[3]	-	11.0	-	dB
ISL	isolation	f = 1843 MHz	[2]	-	23.0	-	dB
		f = 1960 MHz	[4]	-	23.0	-	dB
		f = 2140 MHz	[3]	-	23.0	-	dB
NF	noise figure	f = 1843 MHz	[1][2][5]	-	0.80	1.4	dB
		f = 1960 MHz	[1][4][5]	-	0.85	1.4	dB
		f = 2140 MHz	[1][3][5]	-	0.95	1.5	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	f = 1843 MHz	[1][2]	-12.0	-8.0	-	dBm
		f = 1960 MHz	[1][3]	-11.0	-7.0	-	dBm
		f = 2140 MHz	[1][5]	-10.0	-6.0	-	dBm
$IP3_i$	input third-order intercept point	f = 1843 MHz	[1][2]	-3.0	+2.0	-	dBm
		f = 1960 MHz	[1][4]	-2.5	+2.5	-	dBm
		f = 2140 MHz	[1]	-2.0	+3.0	-	dBm
K	Rollett stability factor			1	-	-	-
t_{on}	turn-on time	time from $V_{I(CTRL)}$ ON to 90 % of the gain		-	-	1.7	µs
t_{off}	turn-off time	time from $V_{I(CTRL)}$ OFF to 10 % of the gain		-	-	0.6	µs

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Bypass mode							
I_{CC}	supply current	$V_{I(CTRL)}$ < 0.3 V		-	-	1	µA
G_p	power gain	f = 1843 MHz	[1][2]	-3.6	-2.1	-0.6	dB
		f = 1960 MHz	[1][4]	-4.0	-2.2	-0.7	dB
		f = 2140 MHz	[1][3]	-4.0	-2.5	-1.0	dB
RL_{in}	input return loss	f = 1843 MHz	[2]	-	12.0	-	dB
		f = 1960 MHz	[4]	-	11.0	-	dB
		f = 2140 MHz	[3]	-	10.0	-	dB
RL_{out}	output return loss	f = 1843 MHz	[2]	-	10.0	-	dB
		f = 1960 MHz	[4]	-	9.5	-	dB
		f = 2140 MHz	[3]	-	9.0	-	dB

[1] Guaranteed by device design; not tested in production.
[2] E-UTRA operating band 3 (1805 MHz to 1880 MHz).
[3] E-UTRA operating band 1 (2110 MHz to 2170 MHz).
[4] E-UTRA operating band 2 (1930 MHz to 1990 MHz).
[5] PCB losses are subtracted.

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Table 9. Characteristics at V_{CC} = 2.8 V

1805 MHz ≤ f ≤ 2200 MHz, V_{CC} = 2.8 V, $V_{I(CTRL)}$ ≥ 0.8 V and T_{amb} = 25 °C. Input matched to 50 Ω using a 3.9 nH inductor in series. Unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Δφ	phase variation	between gain mode and bypass mode					
		f = 1843 MHz		-	-	-	deg
		f = 1960 MHz	[1]	-5.0	-	+5.0	deg
		f = 2140 MHz		-	-	-	deg
Gain mode							
I_{CC}	supply current			3.8	5.8	7.8	mA
G_p	power gain	f = 1843 MHz	[1][2]	12.5	14.5	16.5	dB
		f = 1960 MHz	[3]	12.4	14.4	16.4	dB
		f = 2140 MHz	[1][4]	11.7	13.7	15.7	dB
RL_{in}	input return loss	f = 1843 MHz	[2]	-	5.5	-	dB
		f = 1960 MHz	[3]	-	6.5	-	dB
		f = 2140 MHz	[4]	-	7.5	-	dB
RL_{out}	output return loss	f = 1843 MHz	[2]	-	12.0	-	dB
		f = 1960 MHz	[3]	-	12.0	-	dB
		f = 2140 MHz	[4]	-	11.0	-	dB
ISL	isolation	f = 1843 MHz	[2]	-	25.0	-	dB
		f = 1960 MHz	[3]	-	24.0	-	dB
		f = 2140 MHz	[4]	-	23.0	-	dB

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
NF	noise figure	f = 1843 MHz	[1][2][5]	-	0.80	1.4	dB
		f = 1960 MHz	[1][3][5]	-	0.85	1.4	dB
		f = 2140 MHz	[1][4][5]	-	0.95	1.5	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	f = 1843 MHz	[1][2]	-7.5	-3.5	-	dBm
		f = 1960 MHz	[1][3]	-7.5	-3.5	-	dBm
		f = 2140 MHz	[1][4]	-6.5	-2.5	-	dBm
$IP3_i$	input third-order intercept point	f = 1843 MHz	[1][2]	-2.5	+2.5	-	dBm
		f = 1960 MHz	[1][3]	-1.5	+3.5	-	dBm
		f = 2140 MHz	[1][4]	-1.0	+4.0	-	dBm
K	Rollett stability factor			1	-	-	
t_{on}	turn-on time	time from $V_{I(CTRL)}$ ON to 90 % of the gain		-	-	1.3	µs
t_{off}	turn-off time	time from $V_{I(CTRL)}$ OFF to 10 % of the gain		-	-	0.3	µs
Bypass mode							
I_{CC}	supply current	$V_{I(CTRL)}$ < 0.3 V		-	-	1	µA
G_p	power gain	f = 1843 MHz	[1][2]	-3.6	-2.1	-0.6	dB
		f = 1960 MHz	[3]	-4.0	-2.2	-0.7	dB
		f = 2140 MHz	[1][4]	-4.0	-2.5	-1.0	dB
RL_{in}	input return loss	f = 1843 MHz	[2]	-	12	-	dB
		f = 1960 MHz	[3]	-	11	-	dB
		f = 2140 MHz	[4]	-	10	-	dB
RL_{out}	output return loss	f = 1843 MHz	[2]	-	10	-	dB
		f = 1960 MHz	[3]	-	10	-	dB
		f = 2140 MHz	[4]	-	9	-	dB

[1] Guaranteed by device design; not tested in production.
[2] E-UTRA operating band 3 (1805 MHz to 1880 MHz).
[3] E-UTRA operating band 2 (1930 MHz to 1990 MHz).
[4] E-UTRA operating band 1 (2110 MHz to 2170 MHz).
[5] PCB losses are subtracted.

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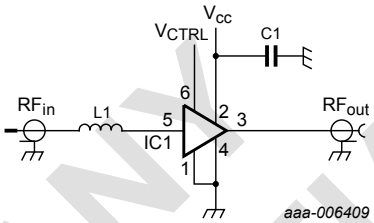
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13 Application information

13.1 LTE LNA



For a list of components, see Table 10.

Figure 3. Schematics LTE LNA evaluation board

Table 10. List of components

For schematics, see Figure 3.

Component	Description	Value	Remarks
C1	decoupling capacitor	1 µF	to suppress power supply noise
IC1	BGS8M2	-	NXP Semiconductors
L1	high-quality matching inductor	3.9 nH	Murata LQW15A

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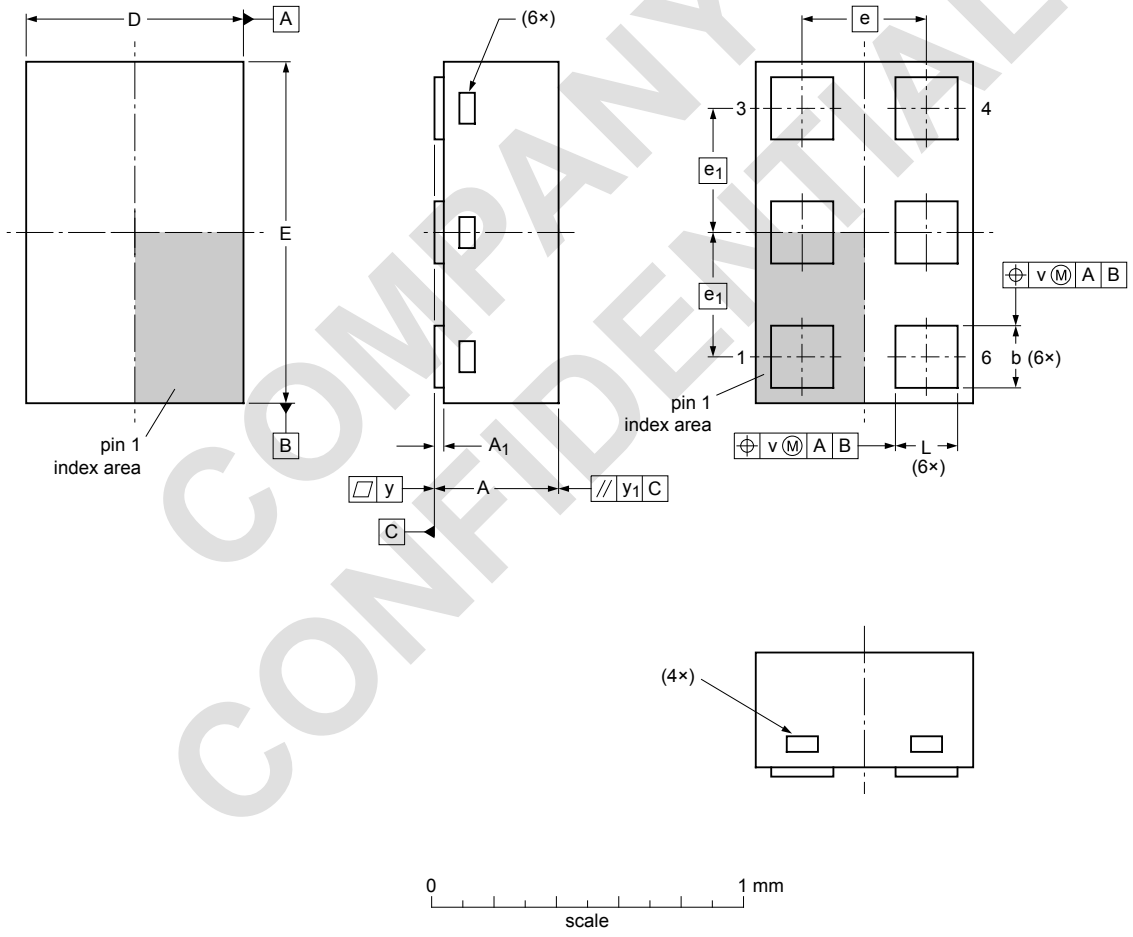
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14 Package outline

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1.1 x 0.7 x 0.37 mm **SOT1232**



Dimensions (mm are the original dimensions)

Unit		A	A_1	D	E	e_1	e	b	L	V	Y	Y_1
	min	0.34		0.65	1.05			0.17	0.17			
mm	nom	0.37		0.70	1.10	0.4	0.4	0.20	0.20	0.1	0.05	0.1
	max	0.40	0.04	0.75	1.15			0.25	0.25			

Note
1. Dimension A is including plating thickness.

sot1232_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1232						~~13-04-12~~ 13-11-08

Figure 4. Package outline SOT1232 (XSON6)

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15 Handling information

CAUTION	
 msc896	This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices. Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A*, or equivalent standards.

16 Abbreviations

Table 11. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
HBM	Human Body Model
LTE	Long-Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
PCB	Printed-Circuit Board
SiGe:C	Silicon Germanium Carbon

17 Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGS8M2 v.4	20180612	product data sheet	-	BGS8M2 v.3.1
Modifications:	changed $V_{I(CTRL)}$ Max ON state value to V_{cc} at recommended operating conditions			
BGS8M2 v.3.1	20180517	product data sheet	-	BGS8M2 v.3
Modifications:	inserted the standard ESD picture at handling information			
BGS8M2 v.3	20170117	product data sheet	-	BGS8M2 v.2
Modifications:	• Section 1: added LTE3001M according to our new naming convention			
BGS8M2 v.2	20160329	product data sheet	-	BGS8M2 v.1
Modifications:	• added phase variation Table 8 on page 5 and Table 9 on page 6			
BGS8M2 v.1	20151222	Product data sheet	-	-

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18 Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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